

Appl. No. 09/894,717  
Amdt. dated May 5, 2003  
Reply to Office action of December 3, 2002

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims**

Claim 1 (currently amended): A semiconductor with integrated monitoring comprising:  
a first light emitting semiconductor device formed on a predetermined substrate;  
a passivation layer formed on top of said first semiconductor device, said passivation  
layer including a window; and  
a light monitoring device formed on top of said passivation layer for monitoring leakage  
light from said first semiconductor device through said window.

Claim 2 (original): The semiconductor as recited in claim 1, wherein said first semiconductor device is an active device.

Claim 3 (currently amended): A The semiconductor with integrated monitoring comprising:  
— a first semiconductor formed on as recited in claim 1, wherein said predetermined  
substrate is a GaAs substrate;  
— a passivation layer formed on top of said first semiconductor device; and  
— a monitoring device formed on top of said passivation layer.

Claim 4 (currently amended): A The semiconductor with integrated monitoring comprising:  
— a first semiconductor formed on as recited in claim 1, wherein said predetermined  
substrate is a InP substrate;  
— a passivation layer formed on top of said first semiconductor device; and  
— a monitoring device formed on top of said passivation layer.

Claim 5 (currently amended): A The semiconductor with integrated monitoring comprising:  
— a first semiconductor formed on as recited in claim 1, wherein said predetermined  
substrate is a GaN substrate;  
— a passivation layer formed on top of said first semiconductor device; and

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~~a monitoring device formed on top of said passivation layer.~~

Claim 6 (cancelled)

Claim 7 (original): The semiconductor as recited in claim 1, wherein said first semiconductor device is a light emitting device.

Claim 8 (original): The semiconductor as recited in claim 6, wherein said light emitting device is a laser.

Claim 9 (original): The semiconductor as recited in claim 8, wherein said laser is a vertical cavity surface emitting laser (VCSEL).

Claim 10 (original): The semiconductor as recited in claim 1, wherein said monitoring device is a light transmitting device.

Claim 11 (original): The semiconductor as recited in claim 1, wherein said monitoring device is a light receiving device.

Claim 12 (original): The semiconductor as recited in claim 10, wherein said light transmitting device is a photodiode.

Claim 13 (original): The semiconductor as recited in claim 11, wherein said light receiving device is a photodetector.

Claims 14-22 (cancelled)